

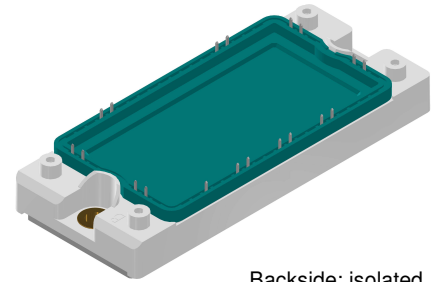
# Standard Rectifier Module

3~ Rectifier	Brake Chopper
$V_{RRM} = 1600 \text{ V}$	$V_{CES} = 1200 \text{ V}$
$I_{DAV} = 120 \text{ A}$	$I_{C25} = 120 \text{ A}$
$I_{FSM} = 700 \text{ A}$	$V_{CE(sat)} = 1.8 \text{ V}$

## 3~ Rectifier Bridge + Brake Unit + NTC

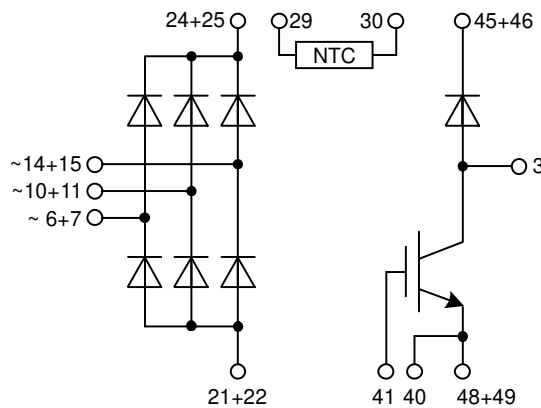
Part number

**VUB116-16NOXT**



Backside: isolated

E72873



### Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current
- NTC

### Applications:

- 3~ Rectifier with brake unit for drive inverters

### Package: E2-Pack

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 17 mm
- Base plate: Copper internally DCB isolated
- Advanced power cycling
- Phase Change Material available

### Terms and Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

- to perform joint risk and quality assessments;

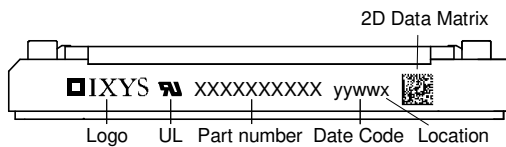
- the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage					1700	V
$V_{RRM}$	max. repetitive reverse blocking voltage					1600	V
$I_R$	reverse current	$V_R = 1600$ V		$T_{VJ} = 25^\circ\text{C}$		100	$\mu\text{A}$
		$V_R = 1600$ V		$T_{VJ} = 150^\circ\text{C}$		1.5	mA
$V_F$	forward voltage drop	$I_F = 40$ A		$T_{VJ} = 25^\circ\text{C}$		1.19	V
		$I_F = 120$ A				1.64	V
		$I_F = 40$ A		$T_{VJ} = 125^\circ\text{C}$		1.12	V
		$I_F = 120$ A				1.70	V
$I_{DAV}$	bridge output current	$T_C = 105^\circ\text{C}$		$T_{VJ} = 150^\circ\text{C}$		120	A
		rectangular	$d = \frac{1}{3}$				
$V_{FO}$	threshold voltage			$T_{VJ} = 150^\circ\text{C}$		0.80	V
$r_F$	slope resistance					7.6	m $\Omega$
						} for power loss calculation only	
$R_{thJC}$	thermal resistance junction to case					0.65	K/W
$R_{thCH}$	thermal resistance case to heatsink				0.1		K/W
$P_{tot}$	total power dissipation			$T_C = 25^\circ\text{C}$		190	W
$I_{FSM}$	max. forward surge current	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		700	A
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		755	A
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		595	A
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		645	A
$I^2t$	value for fusing	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		2.45	kA <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		2.37	kA <sup>2</sup> s
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		1.77	kA <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		1.73	kA <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400$ V; $f = 1$ MHz		$T_{VJ} = 25^\circ\text{C}$		27	pF

Brake IGBT				Ratings					
Symbol	Definition	Conditions	min.	typ.	max.	Unit			
$V_{CES}$	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200	V			
$V_{GES}$	max. DC gate voltage				$\pm 20$	V			
$V_{GEM}$	max. transient gate emitter voltage				$\pm 30$	V			
$I_{C25}$	collector current	$T_C = 25^{\circ}\text{C}$			120	A			
$I_{C80}$		$T_C = 80^{\circ}\text{C}$			84	A			
$P_{tot}$	total power dissipation	$T_C = 25^{\circ}\text{C}$			390	W			
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 75\text{ A}; V_{GE} = 15\text{ V}$			1.8	V			
					2.1	V			
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 3\text{ mA}; V_{GE} = V_{CE}$	5.5	6.0	6.5	V			
$I_{CES}$	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$			0.2	mA			
					0.6	mA			
$I_{GES}$	gate emitter leakage current	$V_{GE} = \pm 20\text{ V}$			500	nA			
$Q_{G(on)}$	total gate charge	$V_{CE} = 600\text{ V}; V_{GE} = 15\text{ V}; I_C = 75\text{ A}$		230		nC			
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600\text{ V}; I_C = 75\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 10\ \Omega$							
$t_r$	current rise time						$T_{VJ} = 125^{\circ}\text{C}$	70	ns
$t_{d(off)}$	turn-off delay time						40	ns	
$t_f$	current fall time						250	ns	
$E_{on}$	turn-on energy per pulse						100	ns	
$E_{off}$	turn-off energy per pulse						6.8	mJ	
$E_{off}$		8.3	mJ						
<b>RBSOA</b>	reverse bias safe operating area	$V_{GE} = \pm 15\text{ V}; R_G = 10\ \Omega$							
$I_{CM}$		$V_{CEK} = 1200\text{ V}$			225	A			
<b>SCSOA</b>	short circuit safe operating area	$V_{CEK} = 1200\text{ V}$							
$t_{SC}$	short circuit duration	$V_{CE} = 900\text{ V}; V_{GE} = \pm 15\text{ V}$			10	$\mu\text{s}$			
$I_{SC}$	short circuit current	$R_G = 10\ \Omega$ ; non-repetitive		300		A			
$R_{thJC}$	thermal resistance junction to case				0.32	K/W			
$R_{thCH}$	thermal resistance case to heatsink				0.15	K/W			
Brake Diode									
$V_{RRM}$	max. repetitive reverse voltage				1200	V			
$I_{F25}$	forward current				48	A			
$I_{F80}$					32	A			
$V_F$	forward voltage	$I_F = 30\text{ A}$			2.75	V			
					1.99	V			
$I_R$	reverse current	$V_R = V_{RRM}$			0.25	mA			
					1	mA			
$Q_{rr}$	reverse recovery charge	$V_R = 600\text{ V}$ $-di_f/dt = 400\text{ A}/\mu\text{s}$ $I_F = 30\text{ A}$							
$I_{RM}$	max. reverse recovery current						$T_{VJ} = 125^{\circ}\text{C}$	1.8	$\mu\text{C}$
$t_{rr}$	reverse recovery time						23	A	
$R_{thJC}$	thermal resistance junction to case				0.9	K/W			
$R_{thCH}$	thermal resistance case to heatsink				0.3	K/W			

Package E2-Pack		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			200	A
$T_{VJ}$	virtual junction temperature		-40		150	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		125	°C
<b>Weight</b>				176		g
$M_D$	mounting torque		3		6	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Apb}$		terminal to backside	12.0			mm
$V_{ISOL}$	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUB116-16NOXT	VUB116-16NOXT	Box	6	510755

### Temperature Sensor NTC

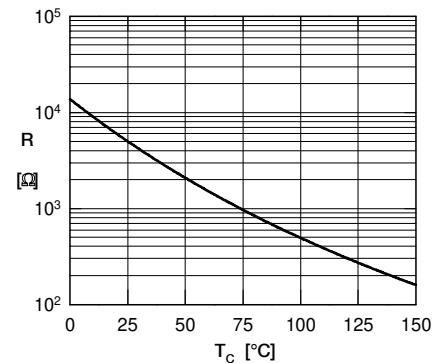
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$R_{25}$	resistance	$T_{VJ} = 25^\circ$	4.75	5	5.25	k $\Omega$
$B_{25/50}$	temperature coefficient			3375		K

### Equivalent Circuits for Simulation

\* on die level

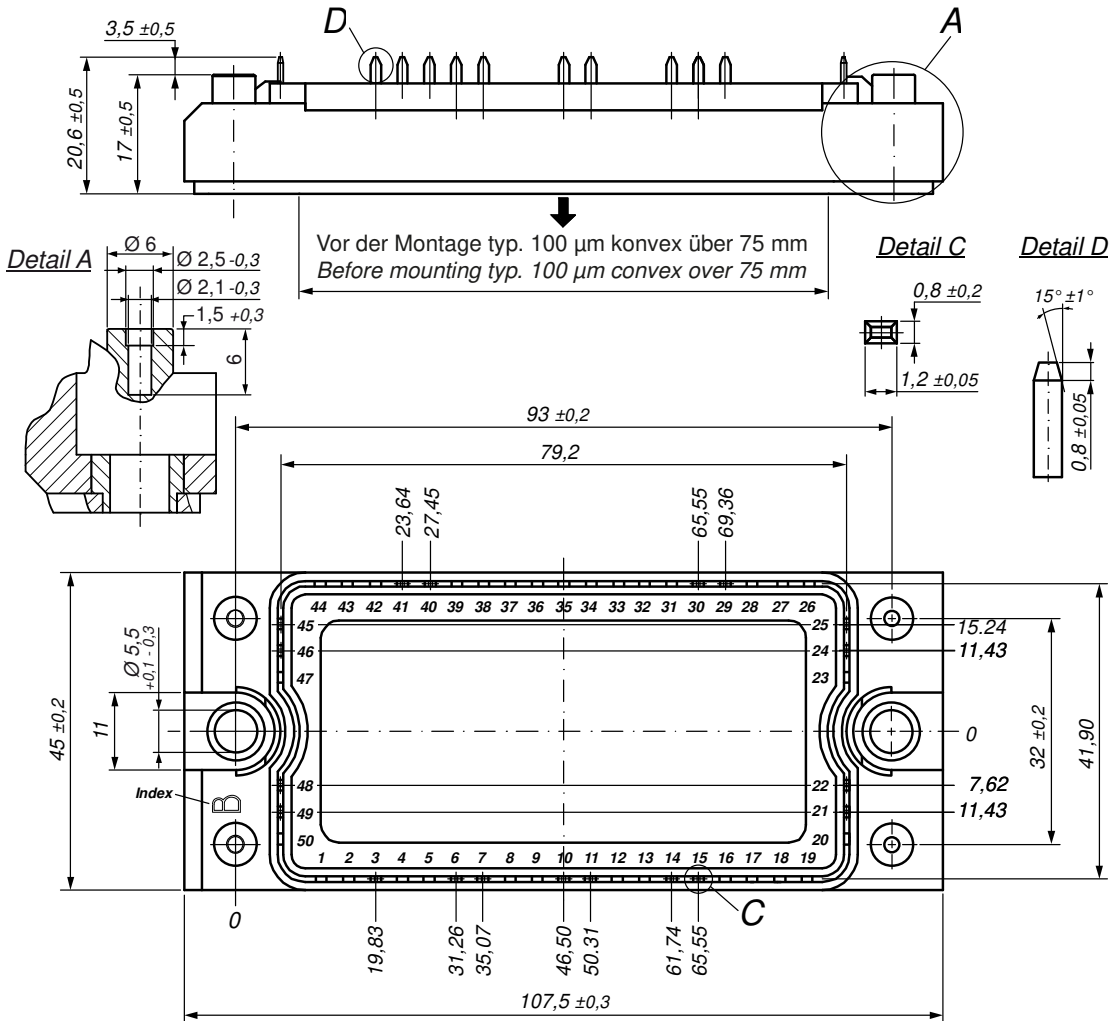
$T_{VJ} = 150^\circ\text{C}$

		Rectifier	Brake IGBT	Brake Diode	
$V_0$	threshold voltage	0.8	1.1	1.31	V
$R_0$	slope resistance *	4.5	17.9	8	m $\Omega$



Typ. NTC resistance vs. temperature

## Outlines E2-Pack

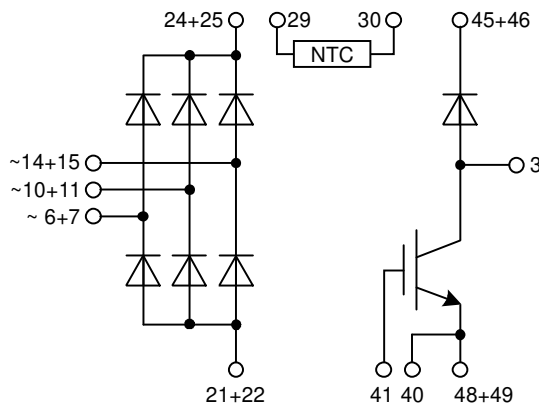


### Bemerkung / Note:

- Nichttolerierete Maße nach / Measure without tolerances according DIN ISO 2768-T1-m
- PCB-Lochmuster / PCB hole pattern: **see pin position**
- Toleranz Pin-Position und PCB-Lochmuster / Tolerance of pin position and PCB hole pattern:  $\oplus 0.1$
- Montageanleitung / Mounting instruction: [www.ixys.com](http://www.ixys.com) **Application note IXAN0024**

### Detail A: PCB-Montage / Mounting on PCB <sup>L</sup>

- Empfohlene, selbstschneidende Schraube / Recommended, self-tapping screw: **EJOT PT®** (Größe / size: **K25**) <sup>L</sup>
- Max. Schraubenlänge / Max. screw length: **PCB-Dicke / thickness + 6 mm** (max. Lochtiefe / hole depth) <sup>L</sup>
- Empfohlenes Drehmoment / Recommended mounting torque: **1.5 Nm**



Rectifier

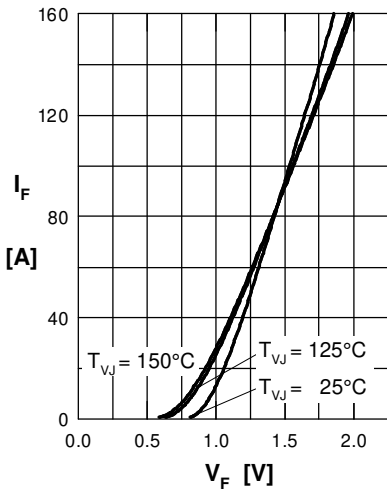


Fig. 1 Forward current versus voltage drop per diode

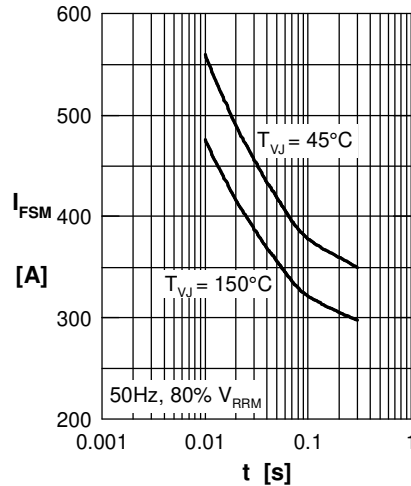


Fig. 2 Surge overload current vs. time per diode

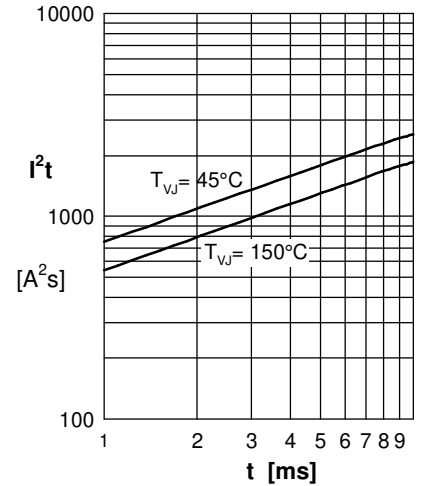


Fig. 3  $I^2t$  versus time per diode

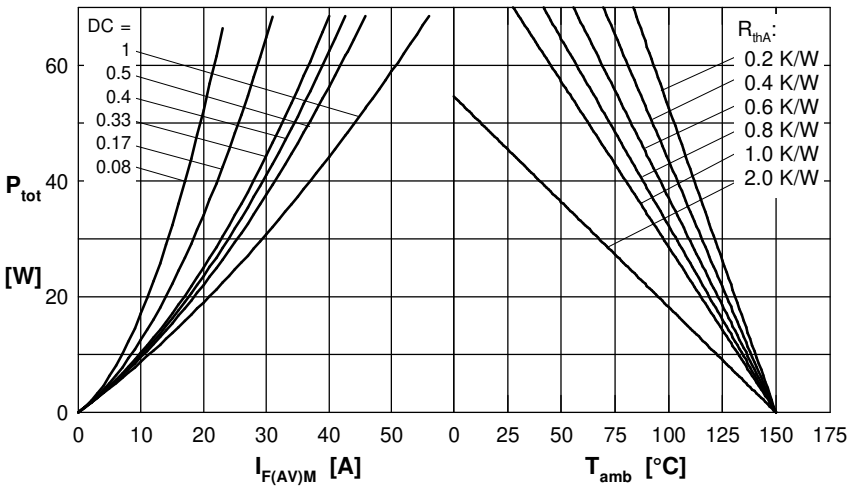


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

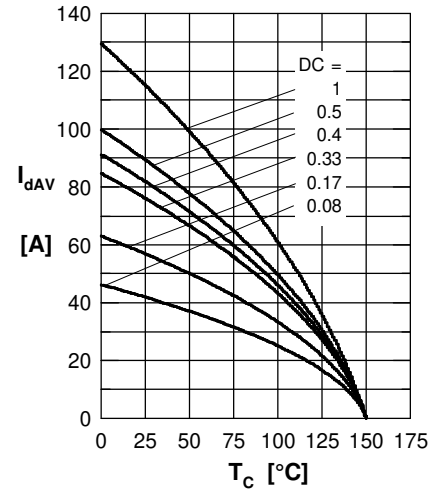


Fig. 5 Max. forward current vs. case temperature per diode

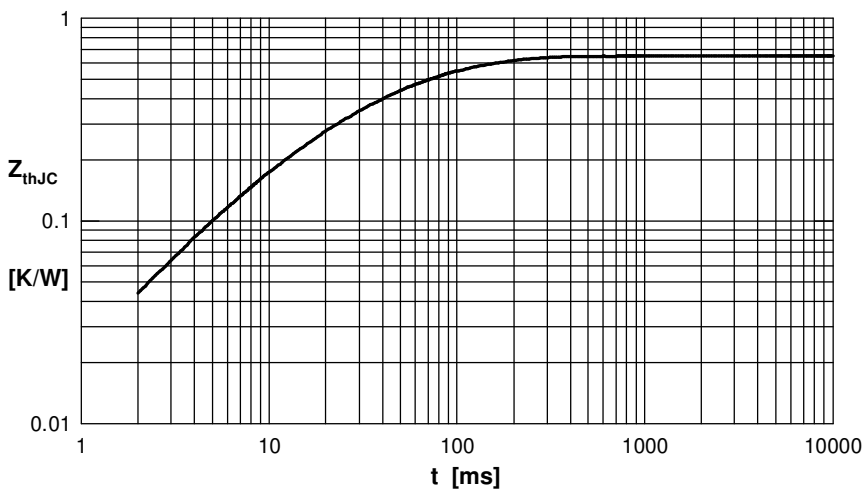


Fig. 6 Transient thermal impedance junction to case vs. time per diode

$R_i$	$t_i$
0.085	0.012
0.041	0.007
0.309	0.036
0.215	0.102

## Brake IGBT

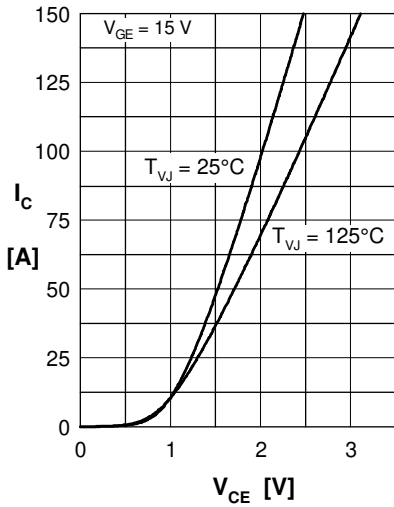


Fig. 1 Typ. output characteristics

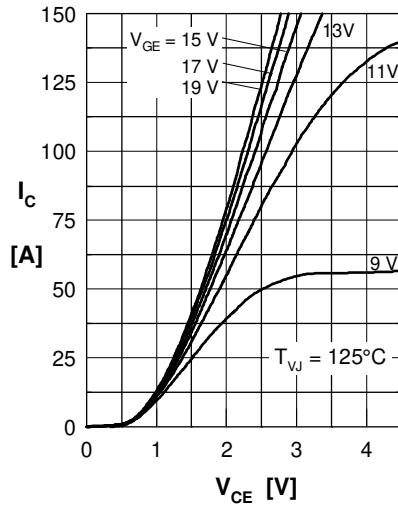


Fig. 2 Typ. output characteristics

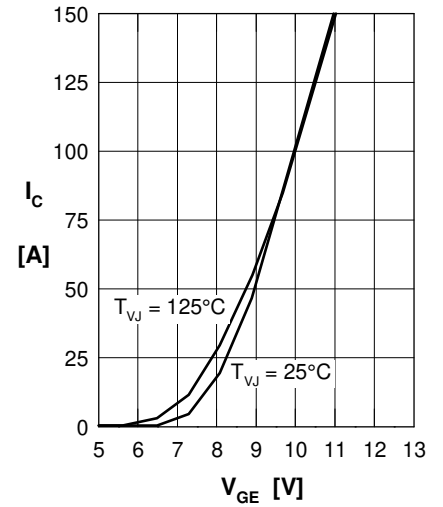


Fig. 3 Typ. transfer characteristics

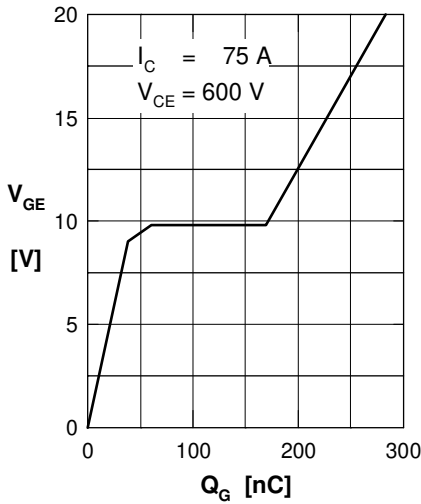


Fig. 4 Typ. turn-on gate charge

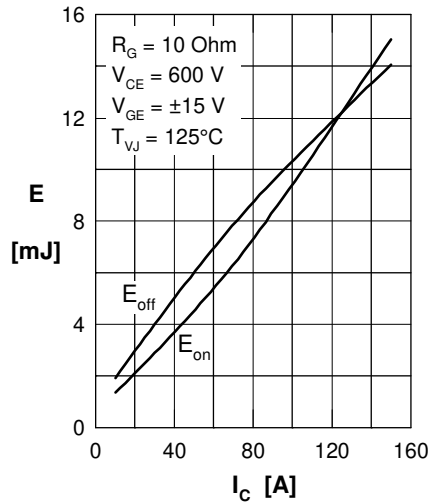


Fig. 5 Typ. switching energy versus collector current

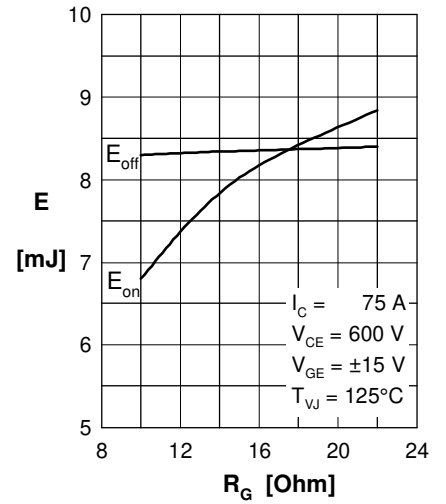


Fig. 6 Typ. switching energy versus gate resistance

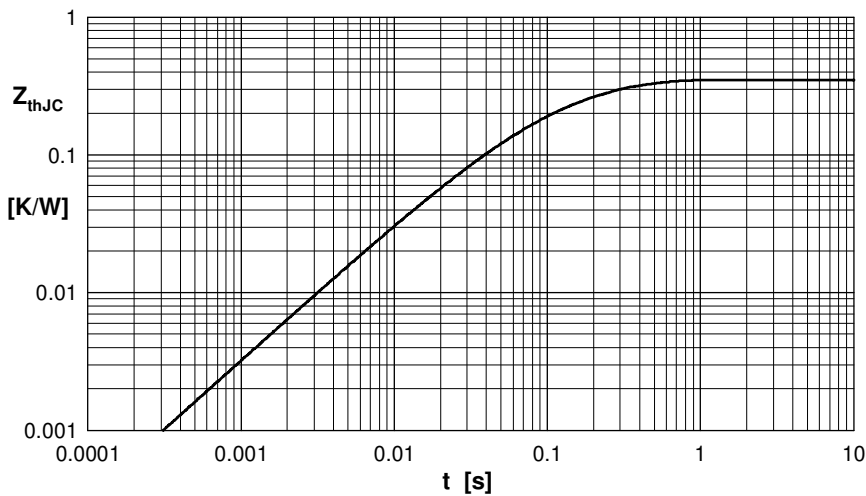


Fig. 7 Typ. transient thermal impedance junction to case

**Brake Diode**

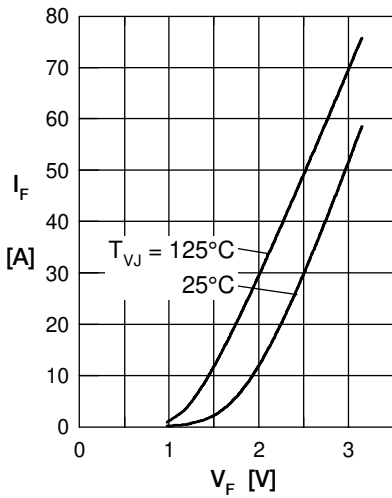


Fig. 1 Forward current  $I_F$  vs.  $V_F$

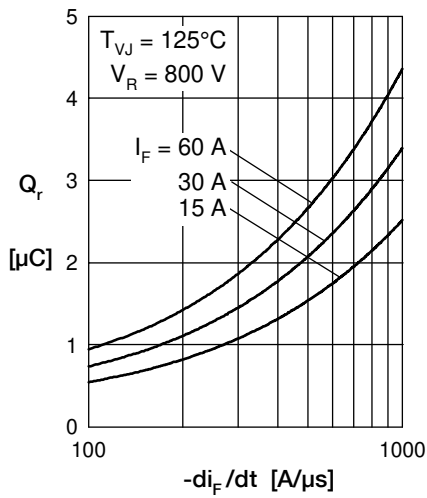


Fig. 2 Typ. reverse recovery charge  $Q_r$  versus  $-di_F/dt$

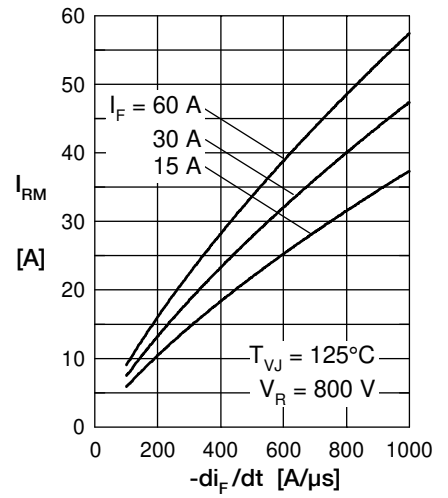


Fig. 3 Typ. peak reverse current  $I_{RM}$  versus  $-di_F/dt$

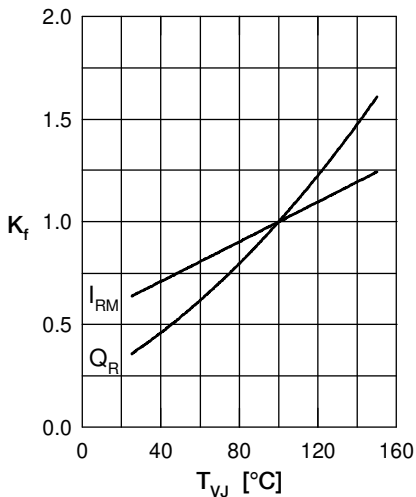


Fig. 4 Dynamic parameters  $Q_r$ ,  $I_{RM}$  versus  $T_{VJ}$

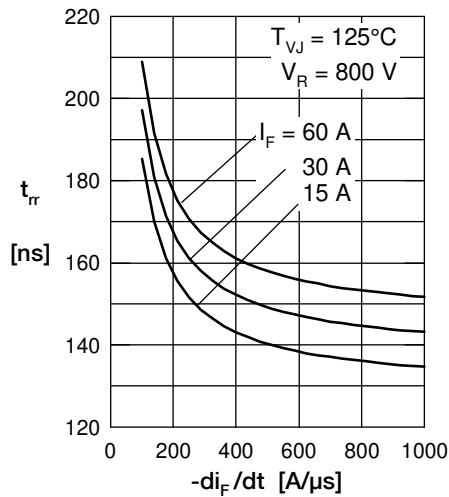


Fig. 5 Typ. recovery time  $t_{rr}$  versus  $-di_F/dt$

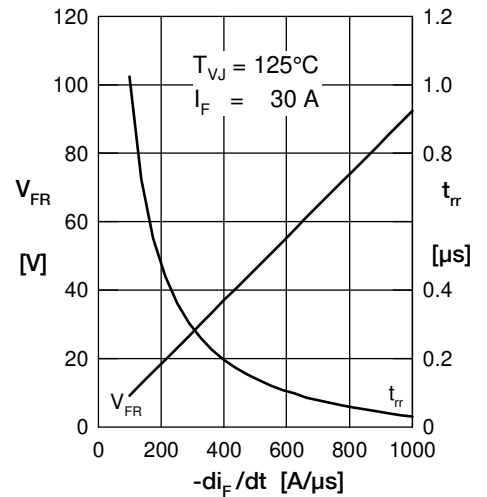


Fig. 6 Typ. peak forward voltage  $V_{FR}$  and  $t_{rr}$  versus  $di_F/dt$

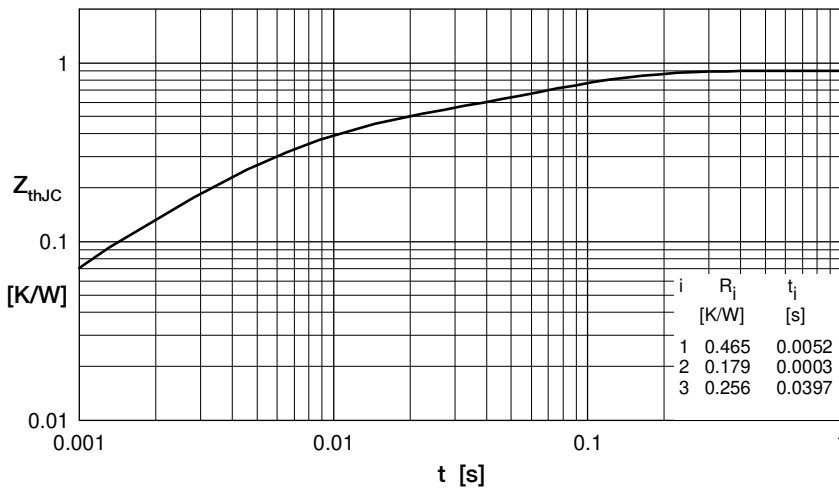


Fig. 7 Transient thermal impedance junction to case